NSN 5961-00-430-6884

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-430-6884 **Inclosure Material:** Plastic **Overall Length:** Between 0.660 inches and 0.785 inches **Overall Height:** 0.200 inches **Overall Width:** Between 0.290 inches and 0.310 inches **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 50.0 collector to emitter voltage/static/base open all transistor and 80.0 collector to base voltage, dc all transistor and 80.0 collector to emitter voltage, dc with base short-circuited to emitter all transistor and 6.0 emitter to base voltage, instantaneous all transistor **Current Rating Per Characteristic:** 1.50 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 750.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: